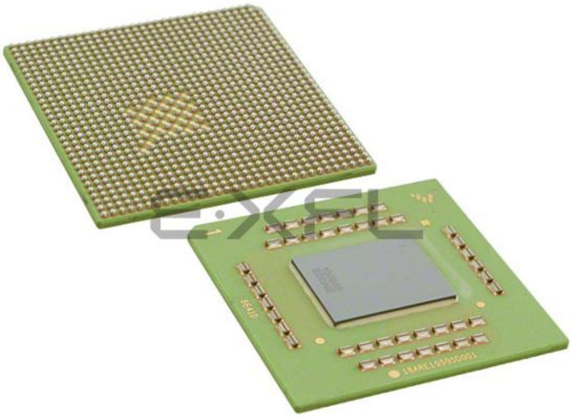
NXP USA Inc. - MC8641HX1000NE Datasheet



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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	994-BCBGA, FCCBGA
Supplier Device Package	994-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641hx1000ne

1.1 Key Features

The following lists an overview of the MPC8641 key feature set:

- Major features of the e600 core are as follows:
  - High-performance, 32-bit superscalar microprocessor that implements the PowerPC ISA
  - Eleven independent execution units and three register files
    - Branch processing unit (BPU)
    - Four integer units (IUs) that share 32 GPRs for integer operands
    - 64-bit floating-point unit (FPU)
    - Four vector units and a 32-entry vector register file (VRs)
    - Three-stage load/store unit (LSU)
  - Three issue queues, FIQ, VIQ, and GIQ, can accept as many as one, two, and three instructions, respectively, in a cycle.
  - Rename buffers
  - Dispatch unit
  - Completion unit
  - Two separate 32-Kbyte instruction and data level 1 (L1) caches
  - Integrated 1-Mbyte, eight-way set-associative unified instruction and data level 2 (L2) cache with ECC
  - 36-bit real addressing
  - Separate memory management units (MMUs) for instructions and data
  - Multiprocessing support features
  - Power and thermal management
  - Performance monitor
  - In-system testability and debugging features
  - Reliability and serviceability
- MPX coherency module (MCM)
  - Ten local address windows plus two default windows
  - Optional low memory offset mode for core 1 to allow for address disambiguation
- Address translation and mapping units (ATMUs)
  - Eight local access windows define mapping within local 36-bit address space
  - Inbound and outbound ATMUs map to larger external address spaces
  - Three inbound windows plus a configuration window on PCI Express
  - Four inbound windows plus a default window on serial RapidIO
  - Four outbound windows plus default translation for PCI Express
  - Eight outbound windows plus default translation for serial RapidIO with segmentation and sub-segmentation support

  - Support for PCI-Express message-shared interrupts (MSIs)
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 133 MHz
  - Eight chip selects support eight external slaves
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and the remote masters
  - Supports transfers to or from any local memory or I/O port
  - Ability to start and flow control each DMA channel from external 3-pin interface
- Device performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter-specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- IEEE 1149.1-compatible, JTAG boundary scan
- Available as 1023 pin Hi-CTE flip chip ceramic ball grid array (FC-CBGA)

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
DDR1 signal	18 36 (half strength mode)	D*n*_GV$_{DD}$ = 2.5 V	4, 9
DDR2 signal	18 36 (half strength mode)	D*n*_GV$_{DD}$ = 1.8 V	1, 5, 9
Local Bus signals	45 25	OV$_{DD}$ = 3.3 V	2, 6
eTSEC/10/100 signals	45	T/LV$_{DD}$ = 3.3 V	6
	30	T/LV$_{DD}$ = 2.5 V	6
DUART, DMA, Multiprocessor Interrupts, System Control & Clocking, Debug, Test, Power management, JTAG and Miscellaneous I/O voltage	45	OV$_{DD}$ = 3.3 V	6
I^{2}C	150	OV$_{DD}$ = 3.3 V	7
SRIO, PCI Express	100	SV$_{DD}$ = 1.1/1.05 V	3, 8

Notes:

1. See the DDR Control Driver registers in the MPC8641D reference manual for more information.
2. Only the following local bus signals have programmable drive strengths: LALE, LAD[0:31], LDP[0:3], LA[27:31], LCKE, LCS[1:2], LWE[0:3], LGPL1, LGPL2, LGPL3, LGPL4, LGPL5, LCLK[0:2]. The other local bus signals have a fixed drive strength of 45 Ω. See the POR Impedance Control register in the MPC8641D reference manual for more information about local bus signals and their drive strength programmability.
3. See Section 17, "Signal Listings," for details on resistor requirements for the calibration of SD*n*_IMP_CAL_TX and SD*n*_IMP_CAL_RX transmit and receive signals.
4. Stub Series Terminated Logic (SSTL-25) type pins.
5. Stub Series Terminated Logic (SSTL-18) type pins.
6. Low Voltage Transistor-Transistor Logic (LVTTL) type pins.
7. Open Drain type pins.
8. Low Voltage Differential Signaling (LVDS) type pins.
9. The drive strength of the DDR interface in half strength mode is at T_j = 105C and at D*n*_GV$_{DD}$ (min).

2.2 Power Up/Down Sequence

The MPC8641 requires its power rails to be applied in a specific sequence in order to ensure proper device operation.

NOTE

The recommended maximum ramp up time for power supplies is 20 milliseconds.

The chronological order of power up is as follows:

1. All power rails other than DDR I/O (D*n*_GV$_{DD}$, and D*n*_MV$_{REF}$).

4 Input Clocks

Table 7 provides the system clock (SYSCLK) DC specifications for the MPC8641.

Table 7. SYSCLK DC Electrical Characteristics (OVDD = 3.3 V ± 165 mV)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	$OV_{DD} + 0.3$	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} ^{1} = 0 V or $V_{IN} = V_{DD}$)	I_{IN}	—	±5	μA

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

4.1 System Clock Timing

Table 8 provides the system clock (SYSCLK) AC timing specifications for the MPC8641.

Table 8. SYSCLK AC Timing Specifications

At recommended operating conditions (see Table 2) with OV_{DD} = 3.3 V ± 165 mV.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
SYSCLK frequency	f_{SYSCLK}	66	—	166.66	MHz	1
SYSCLK cycle time	t_{SYSCLK}	6	—	—	ns	—
SYSCLK rise and fall time	t_{KH}, t_{KL}	0.6	1.0	1.2	ns	2
SYSCLK duty cycle	t_{KHK}/t_{SYSCLK}	40	—	60	%	3
SYSCLK jitter	—	—	—	150	ps	4, 5

Notes:

1. **Caution:** The MPX clock to SYSCLK ratio and e600 core to MPX clock ratio settings must be chosen such that the resulting SYSCLK frequency, e600 (core) frequency, and MPX clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 18.2, "MPX to SYSCLK PLL Ratio," and Section 18.3, "e600 to MPX clock PLL Ratio," for ratio settings.
2. Rise and fall times for SYSCLK are measured at 0.4 V and 2.7 V.
3. Timing is guaranteed by design and characterization.
4. This represents the short term jitter only and is guaranteed by design.
5. The SYSCLK driver's closed loop jitter bandwidth should be <500 kHz at –20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYSCLK drivers with the specified jitter. Note that the frequency modulation for SYSCLK reduces significantly for the spread spectrum source case. This is to guarantee what is supported based on design.

4.1.1 SYSCLK and Spread Spectrum Sources

Spread spectrum clock sources are an increasingly popular way to control electromagnetic interference emissions (EMI) by spreading the emitted noise to a wider spectrum and reducing the peak noise magnitude in order to meet industry and government requirements. These clock sources intentionally add long-term jitter in order to diffuse the EMI spectral content. The jitter specification given in Table 8 considers short-term (cycle-to-cycle) jitter only and the clock generator's cycle-to-cycle output jitter

Figure 5 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (tDDKHMH).

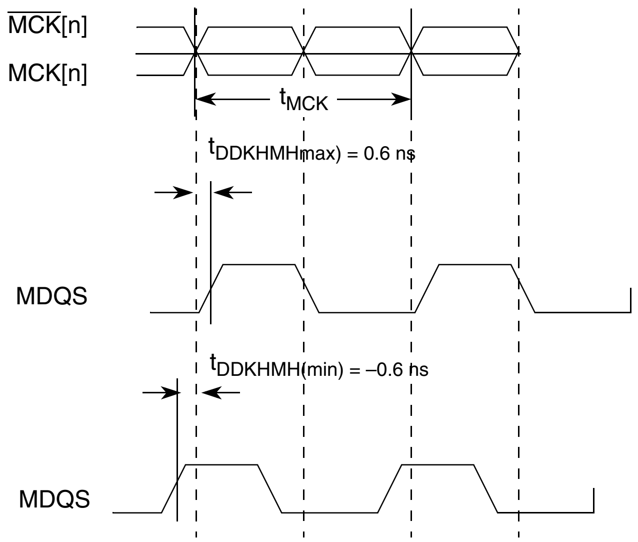

Figure 5. Timing Diagram for tDDKHMH

Figure 6 shows the DDR SDRAM output timing diagram.

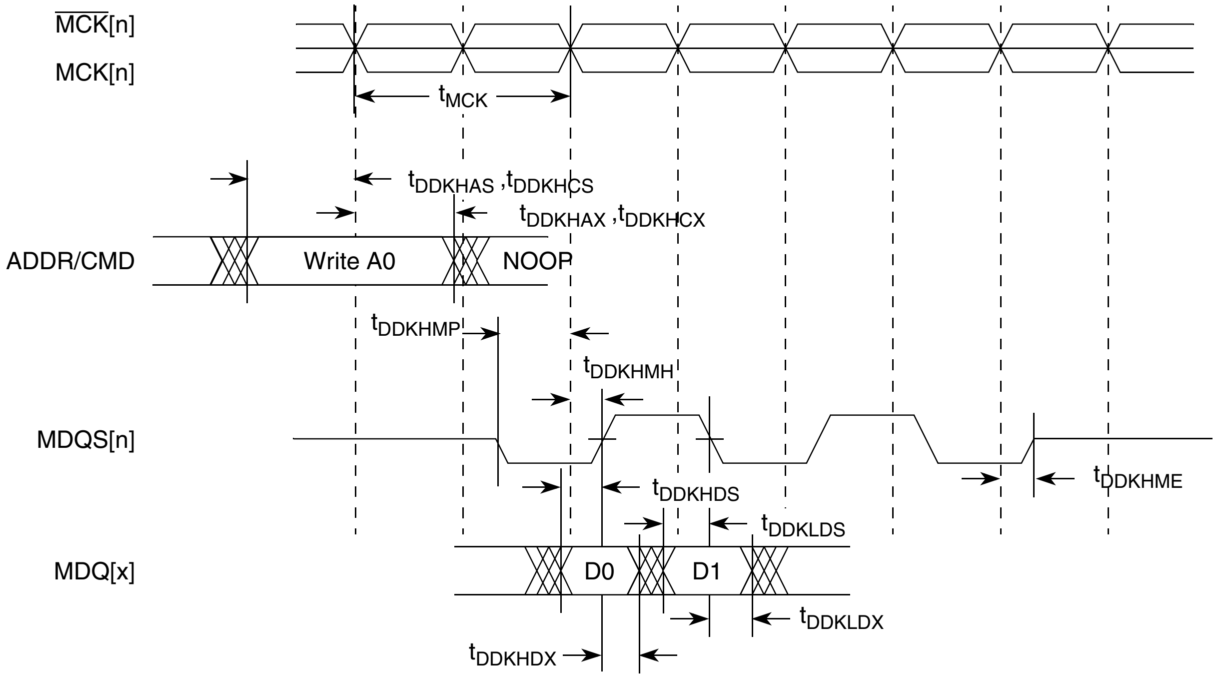

Figure 6. DDR SDRAM Output Timing Diagram

Table 24. GMII, MII, RMII, TBI and FIFO DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit	Notes
Input low current (V_{IN} = GND)	I_{IL}	–600	—	μA	3

Notes:

[1] LV_{DD} supports eTSECs 1 and 2.
[2] TV_{DD} supports eTSECs 3 and 4.
[3] The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

Table 25. GMII, RGMII, RTBI, TBI and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.375	2.625	V	1,2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.00	—	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	—	0.40	V	—
Input high voltage	V_{IH}	1.70	—	V	—
Input low voltage	V_{IL}	—	0.90	V	—
Input high current ($V_{IN} = LV_{DD}$, $V_{IN} = TV_{DD}$)	I_{IH}	—	10	μA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	μA	3

Note:

[1] LV_{DD} supports eTSECs 1 and 2.
[2] TV_{DD} supports eTSECs 3 and 4.
[3] Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit

Table 29. GMII Receive AC Timing Specifications (continued)

At recommended operating conditions with L/TV$_{DD}$ of 3.3 V ± 5% and 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
RX_CLK clock fall time (80%-20%)	t_{GRXF}[2]	—	—	1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.
3. ±100 ppm tolerance on RX_CLK frequency

Figure 11 provides the AC test load for eTSEC.

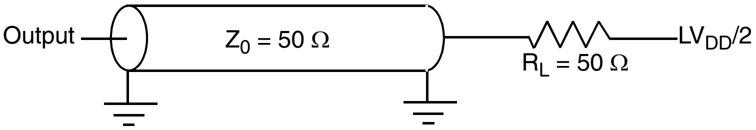

Figure 11. eTSEC AC Test Load

Figure 12 shows the GMII receive AC timing diagram.

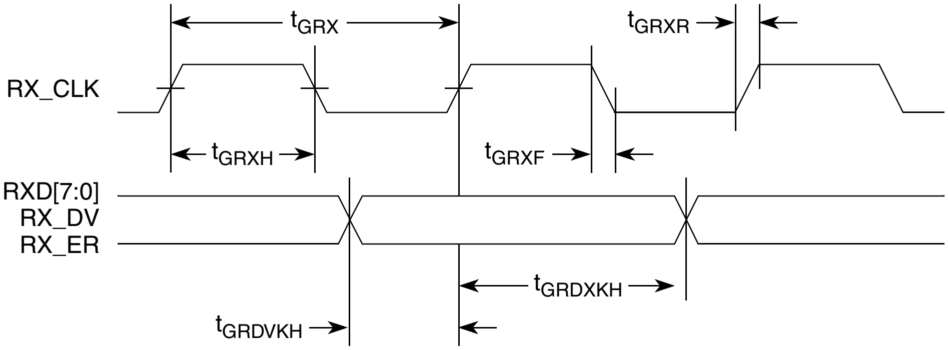

Figure 12. GMII Receive AC Timing Diagram

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8641.

10.1 Local Bus DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the local bus interface operating at OV_{DD} = 3.3 V DC.

Table 40. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} [1] = 0 V or $V_{IN} = OV_{DD}$)	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Note:

1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

Table 41 describes the timing parameters of the local bus interface at OV_{DD} = 3.3 V with PLL enabled. For information about the frequency range of local bus see Section 18.1, “Clock Ranges.”

Table 41. Local Bus Timing Parameters (OV_{DD} = 3.3 V)m - PLL Enabled

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Local Bus Duty Cycle	t_{LBKH}/t_{LBK}	45	55	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	—
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	—

Table 41. Local Bus Timing Parameters (OV_{DD} = 3.3 V)m - PLL Enabled (continued)

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	—
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

Figure 25 provides the AC test load for the local bus.

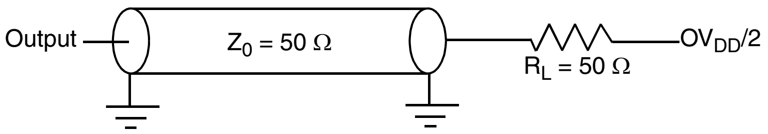

Figure 25. Local Bus AC Test Load

Figure 26 to Figure 31 show the local bus signals.

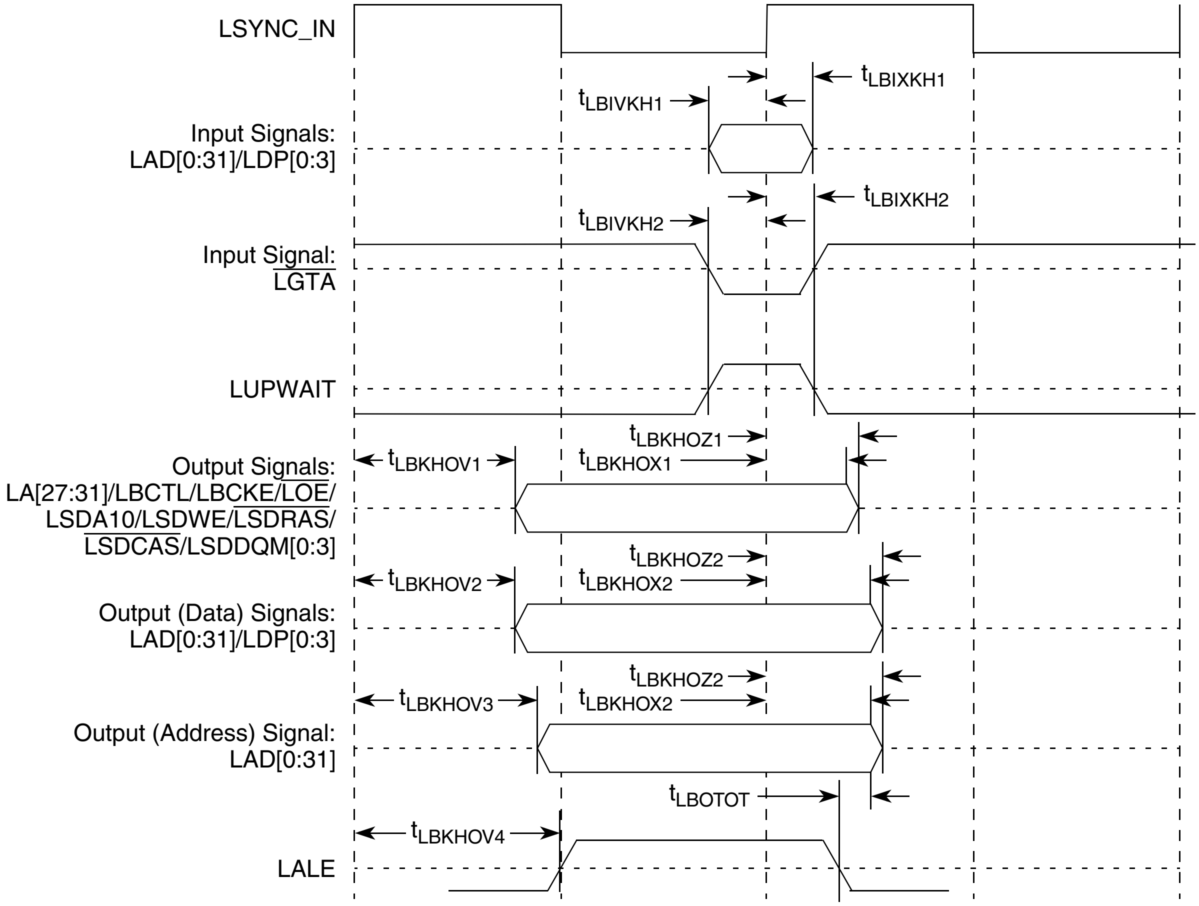

Figure 26. Local Bus Signals (PLL Enabled)

NOTE

PLL bypass mode is recommended when LBIU frequency is at or below 83 MHz. When LBIU operates above 83 MHz, LBIU PLL is recommended to be enabled.

Table 42 describes the general timing parameters of the local bus interface at OV_{DD} = 3.3 V with PLL bypassed.

Table 42. Local Bus Timing Parameters—PLL Bypassed

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	12	—	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	45	55	%	—
Internal launch/capture clock to LCLK delay	t_{LBKHKT}	2.3	3.9	ns	8
Input setup to local bus clock (except LGTA/LUPWAIT)	$t_{LBIVKH1}$	5.7	—	ns	4, 5
LGTA/LUPWAIT input setup to local bus clock	$t_{LBIVKL2}$	5.6	—	ns	4, 5
Input hold from local bus clock (except LGTA/LUPWAIT)	$t_{LBIXKH1}$	–1.8	—	ns	4, 5

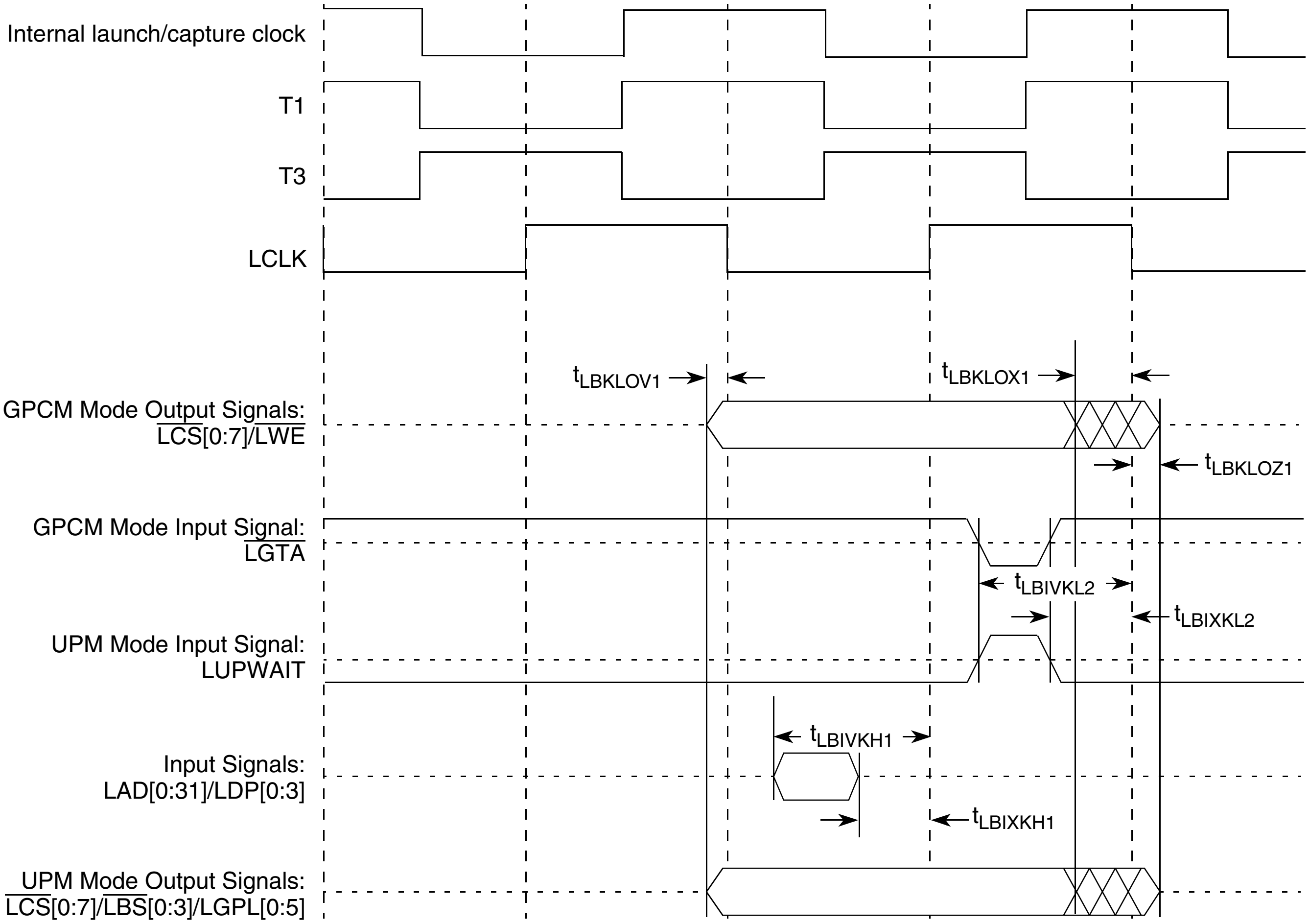

Figure 29. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (clock ratio of 4) (PLL Bypass Mode)

Table 45. I^2C DC Electrical Characteristics (continued)

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. Refer to the *MPC8641 Integrated Host Processor Reference Manual* for information on the digital filter used.
3. I/O pins will obstruct the SDA and SCL lines if OV_{DD} is switched off.

12.2 I^2C AC Electrical Specifications

Table 46 provides the AC timing parameters for the I^2C interfaces.

Table 46. I^2C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 45).

Parameter	Symbol [1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL} [4]	1.3	—	μs
High period of the SCL clock	t_{I2CH} [4]	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH} [4]	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL} [4]	0.6	—	μs
Data setup time	t_{I2DVKH} [4]	100	—	ns
Data input hold time: CBUS compatible masters I^2C bus devices	t_{I2DXKL}	 — 0 [2]	 — —	 μs
Rise time of both SDA and SCL signals	t_{I2CR}	$20 + 0.1\ C_B$ [5]	300	ns
Fall time of both SDA and SCL signals	t_{I2CF}	$20 + 0.1\ C_b$ [5]	300	ns
Data output delay time	t_{I2OVKL}	—	0.9 [3]	μs
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	μs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V

MPC8641D SerDes reference clock input's DC requirement, AC-coupling has to be used. Figure 45 assumes that the LVPECL clock driver's output impedance is 50 Ω. R1 is used to DC-bias the LVPECL outputs prior to AC-coupling. Its value could be ranged from 140 Ω to 240 Ω depending on clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50-Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the MPC8641D SerDes reference clock's differential input amplitude requirement (between 200 mV and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600mV, the attenuation factor is 0.67, which requires R2 = 25 Ω. Please consult clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.

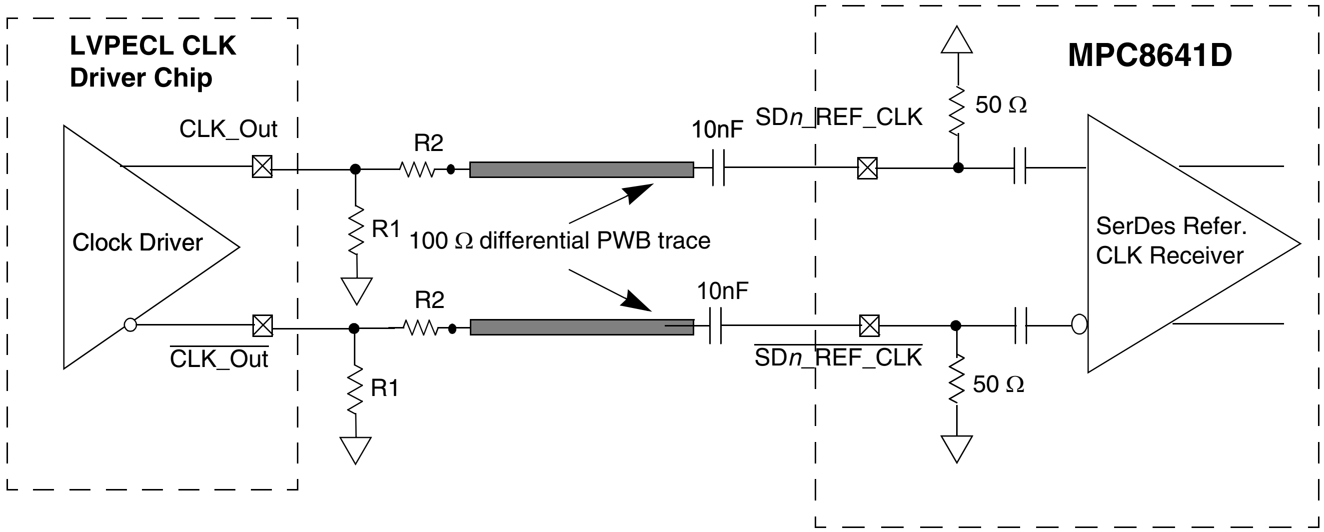

Figure 45. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

14.1 DC Requirements for PCI Express SD*n*_REF_CLK and $\overline{\mathrm{SD}n\_\mathrm{REF}\_\mathrm{CLK}}$

For more information, see Section 13.2, “SerDes Reference Clocks.”

14.2 AC Requirements for PCI Express SerDes Clocks

Table 48 lists AC requirements.

Table 48. SD*n*_REF_CLK and $\overline{\mathrm{SD}n\_\mathrm{REF}\_\mathrm{CLK}}$ AC Requirements

Symbol	Parameter Description	Min	Typical	Max	Units	Notes
t_{REF}	REFCLK cycle time	—	10	—	ns	—
t_{REFCJ}	REFCLK cycle-to-cycle jitter. Difference in the period of any two adjacent REFCLK cycles	—	—	100	ps	—
t_{REFPJ}	Phase jitter. Deviation in edge location with respect to mean edge location	–50	—	50	ps	—

14.3 Clocking Dependencies

The ports on the two ends of a link must transmit data at a rate that is within 600 parts per million (ppm) of each other at all times. This is specified to allow bit rate clock sources with a +/– 300 ppm tolerance.

14.4 Physical Layer Specifications

The following is a summary of the specifications for the physical layer of PCI Express on this device. For further details as well as the specifications of the Transport and Data Link layer please use the PCI EXPRESS Base Specification. REV. 1.0a document.

14.4.1 Differential Transmitter (TX) Output

Table 49 defines the specifications for the differential output at all transmitters (TXs). The parameters are specified at the component pins.

Table 49. Differential Transmitter (TX) Output Specifications

Symbol	Parameter	Min	Nom	Max	Units	Comments
UI	Unit Interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for Spread Spectrum Clock dictated variations. See Note 1.
$V_{TX\text{-}DIFFp\text{-}p}$	Differential Peak-to-Peak Output Voltage	0.8	—	1.2	V	$V_{TX\text{-}DIFFp\text{-}p} = 2*\lvert V_{TX\text{-}D+} - V_{TX\text{-}D-}\rvert$ See Note 2.
$V_{TX\text{-}DE\text{-}RATIO}$	De- Emphasized Differential Output Voltage (Ratio)	–3.0	–3.5	–4.0	dB	Ratio of the $V_{TX\text{-}DIFFp\text{-}p}$ of the second and following bits after a transition divided by the $V_{TX\text{-}DIFFp\text{-}p}$ of the first bit after a transition. See Note 2.

Table 58. Transmitter Differential Output Eye Diagram Parameters

Transmitter Type	V_{DIFF}min (mV)	V_{DIFF}max (mV)	A (UI)	B (UI)
1.25 GBaud short range	250	500	0.175	0.39
1.25 GBaud long range	400	800	0.175	0.39
2.5 GBaud short range	250	500	0.175	0.39
2.5 GBaud long range	400	800	0.175	0.39
3.125 GBaud short range	250	500	0.175	0.39
3.125 GBaud long range	400	800	0.175	0.39

15.7 Receiver Specifications

LP-Serial receiver electrical and timing specifications are stated in the text and tables of this section.

Receiver input impedance shall result in a differential return loss better that 10 dB and a common mode return loss better than 6 dB from 100 MHz to (0.8)*(Baud Frequency). This includes contributions from on-chip circuitry, the chip package and any off-chip components related to the receiver. AC coupling components are included in this requirement. The reference impedance for return loss measurements is 100 Ohm resistive for differential return loss and 25 Ohm resistive for common mode.

Table 59. Receiver AC Timing Specifications—1.25 GBaud

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential Input Voltage	V_{IN}	200	1600	mV p-p	Measured at receiver
Deterministic Jitter Tolerance	J_D	0.37	—	UI p-p	Measured at receiver
Combined Deterministic and Random Jitter Tolerance	J_{DR}	0.55	—	UI p-p	Measured at receiver
Total Jitter Tolerance[1]	J_T	0.65	—	UI p-p	Measured at receiver
Multiple Input Skew	S_{MI}	—	24	ns	Skew at the receiver input between lanes of a multilane link
Bit Error Rate	BER	—	10^{-12}	—	—
Unit Interval	UI	800	800	ps	+/– 100 ppm

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 55. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.

8. Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).

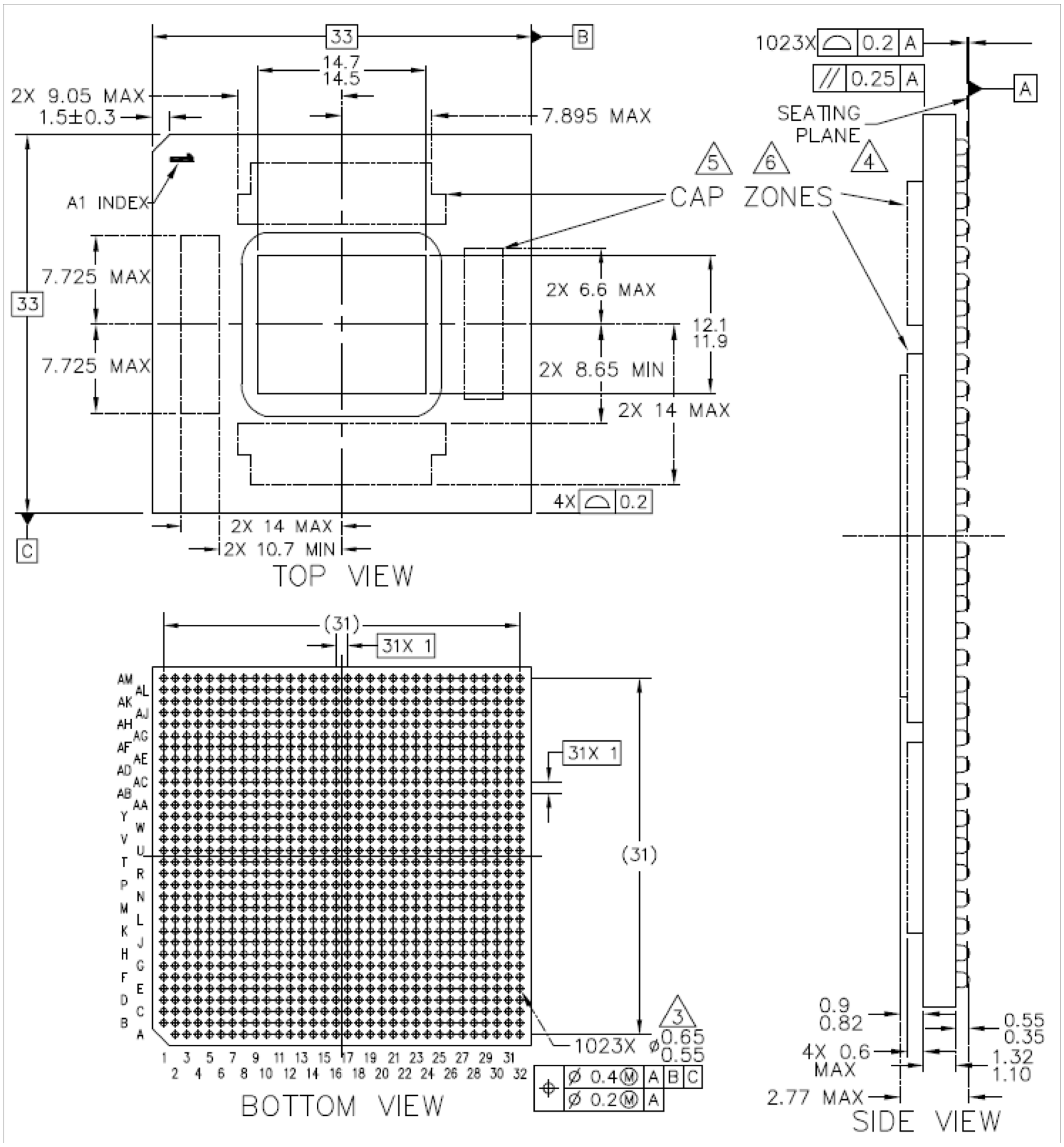

Figure 58. MPC8641D Lead-Free FC-CBGA Dimensions

NOTES for Figure 58

1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is defined by the spherical crowns of the solder balls.
5. Capacitors may not be present on all devices.
6. Caution must be taken not to short capacitors or expose metal capacitor pads on package top.
7. All dimensions symmetrical about centerlines unless otherwise specified.

8. Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).

Table 63. MPC8641 Signal Reference by Functional Block (continued)

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
TSEC1_TXD[0:7]/ GPOUT[0:7]	AF25, AC23,AG24, AG23, AE24, AE23, AE22, AD22	O	LV_{DD}	6, 10
TSEC1_TX_EN	AB22	O	LV_{DD}	36
TSEC1_TX_ER	AH26	O	LV_{DD}	—
TSEC1_TX_CLK	AC22	I	LV_{DD}	40
TSEC1_GTX_CLK	AH25	O	LV_{DD}	41
TSEC1_CRS	AM24	I/O	LV_{DD}	37
TSEC1_COL	AM25	I	LV_{DD}	—
TSEC1_RXD[0:7]/ GPIN[0:7]	AL25, AL24, AK26, AK25, AM26, AF26, AH24, AG25	I	LV_{DD}	10
TSEC1_RX_DV	AJ24	I	LV_{DD}	—
TSEC1_RX_ER	AJ25	I	LV_{DD}	—
TSEC1_RX_CLK	AK24	I	LV_{DD}	40
eTSEC Port 2 Signals[5]				
TSEC2_TXD[0:3]/ GPOUT[8:15]	AB20, AJ23, AJ22, AD19	O	LV_{DD}	6, 10
TSEC2_TXD[4]/ GPOUT[12]	AH23	O	LV_{DD}	6,10, 38
TSEC2_TXD[5:7]/ GPOUT[13:15]	AH21, AG22, AG21	O	LV_{DD}	6, 10
TSEC2_TX_EN	AB21	O	LV_{DD}	36
TSEC2_TX_ER	AB19	O	LV_{DD}	6, 38
TSEC2_TX_CLK	AC21	I	LV_{DD}	40
TSEC2_GTX_CLK	AD20	O	LV_{DD}	41
TSEC2_CRS	AE20	I/O	LV_{DD}	37
TSEC2_COL	AE21	I	LV_{DD}	—
TSEC2_RXD[0:7]/ GPIN[8:15]	AL22, AK22, AM21, AH20, AG20, AF20, AF23, AF22	I	LV_{DD}	10
TSEC2_RX_DV	AC19	I	LV_{DD}	—
TSEC2_RX_ER	AD21	I	LV_{DD}	—
TSEC2_RX_CLK	AM22	I	LV_{DD}	40
eTSEC Port 3 Signals[5]				
TSEC3_TXD[0:3]	AL21, AJ21, AM20, AJ20	O	TV_{DD}	6
TSEC3_TXD[4]/	AM19	O	TV_{DD}	—
TSEC3_TXD[5:7]	AK21, AL20, AL19	O	TV_{DD}	6

18.4.1 SYSCLK to Platform Frequency Options

Table 70 shows some SYSCLK frequencies and the expected MPX frequency values based on the MPX clock to SYSCLK ratio. Note that frequencies between 400 MHz and 500 MHz are NOT supported on the platform. See note regarding *cfg_platform_freq* in Section 17, "Signal Listings," because it is a reset configuration pin that is related to platform frequency.

Table 70. Frequency Options of SYSCLK with Respect to Platform/MPX Clock Speed

MPX to SYSCLK Ratio	SYSCLK (MHz)					
	66	83	100	111	133	167
	Platform/MPX Frequency (MHz)[1]					
2						
3					400	500
4			400		533	
5			500	555		
6	400	500	600			
8	533					
9	600					

[1] SYSCLK frequency range is 66-167 MHz. Platform clock/ MPX frequency range is 400 MHz, 500-600 MHz.

18.4.2 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency <= platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 127 MHz

For FIFO encoded mode:

FIFO TX/RX clock frequency <= platform clock frequency/3.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency should be no more than 167 MHz

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18930 West 78th St.
Chanhassen, MN 55317
Internet: www.bergquistcompany.com

Chomerics, Inc. 781-935-4850
77 Dragon Ct.
Woburn, MA 01801
Internet: www.chomerics.com

Dow-Corning Corporation 800-248-2481
Corporate Center
PO Box 994
Midland, MI 48686-0994
Internet: www.dowcorning.com

Shin-Etsu MicroSi, Inc. 888-642-7674
10028 S. 51st St.
Phoenix, AZ 85044
Internet: www.microsi.com

Thermagon Inc. 888-246-9050
4707 Detroit Ave.
Cleveland, OH 44102
Internet: www.thermagon.com

The following section provides a heat sink selection example using one of the commercially available heat sinks.

19.2.3 Heat Sink Selection Example

For preliminary heat sink sizing, the die-junction temperature can be expressed as follows:

$$T_j = T_i + T_r + (R_{\theta JC} + R_{\theta int} + R_{\theta sa}) \times P_d$$

where:

T_j is the die-junction temperature
T_i is the inlet cabinet ambient temperature
T_r is the air temperature rise within the computer cabinet
$R_{\theta JC}$ is the junction-to-case thermal resistance
$R_{\theta int}$ is the adhesive or interface material thermal resistance
$R_{\theta sa}$ is the heat sink base-to-ambient thermal resistance
P_d is the power dissipated by the device

During operation, the die-junction temperatures (T_j) should be maintained less than the value specified in Table 2. The temperature of air cooling the component greatly depends on the ambient inlet air temperature and the air temperature rise within the electronic cabinet. An electronic cabinet inlet-air temperature (T_i) may range from 30° to 40°C. The air temperature rise within a cabinet (T_r) may be in the range of 5° to 10°C. The thermal resistance of the thermal interface material ($R_{\theta int}$) is typically about 0.2°C/W. For example, assuming a T_i of 30°C, a T_r of 5°C, a package $R_{\theta JC} = 0.1$, and a typical power consumption (P_d) of 43.4 W, the following expression for T_j is obtained:

Die-junction temperature: $T_j = 30°C + 5°C + (0.1°C/W + 0.2°C/W + \theta_{sa}) \times 43.4\ W$

For this example, a $R_{\theta sa}$value of 1.32 °C/W or less is required to maintain the die junction temperature below the maximum value of Table 2.

Though the die junction-to-ambient and the heat sink-to-ambient thermal resistances are a common figure-of-merit used for comparing the thermal performance of various microelectronic packaging technologies, one should exercise caution when only using this metric in determining thermal management because no single parameter can adequately describe three-dimensional heat flow. The final die-junction operating temperature is not only a function of the component-level thermal resistance, but the system-level design and its operating conditions. In addition to the component's power consumption, a number of factors affect the final operating die-junction temperature—airflow, board population (local heat flux of adjacent components), heat sink efficiency, heat sink placement, next-level interconnect technology, system air temperature rise, altitude, and so on.

Due to the complexity and variety of system-level boundary conditions for today's microelectronic equipment, the combined effects of the heat transfer mechanisms (radiation, convection, and conduction) may vary widely. For these reasons, we recommend using conjugate heat transfer models for the board as well as system-level designs.

For system thermal modeling, the MPC8641 thermal model is shown in Figure 62. Four cuboids are used to represent this device. The die is modeled as 12.4x15.3 mm at a thickness of 0.86 mm. See Section 3, “Power Characteristics” for power dissipation details. The substrate is modeled as a single block 33x33x1.2 mm with orthotropic conductivity: 13.5 W/(m • K) in the xy-plane and 5.3 W/(m • K) in the z-direction. The die is centered on the substrate. The bump/underfill layer is modeled as a collapsed thermal resistance between the die and substrate with a conductivity of 5.3 W/(m • K) in the thickness dimension of 0.07 mm. Because the bump/underfill is modeled with zero physical dimension (collapsed height), the die thickness was slightly enlarged to provide the correct height. The C5 solder layer is modeled as a cuboid with dimensions 33x33x0.4 mm and orthotropic thermal conductivity of 0.034 W/(m • K) in the xy-plane and 9.6 W/(m • K) in the z-direction. An LGA solder layer would be modeled as a collapsed thermal resistance with thermal conductivity of 9.6W/(m • K) and an effective height of 0.1 mm. The thermal model uses approximate dimensions to reduce grid. Please refer to the case outline for actual dimensions.